[Abstract Guideline (Leave two lines for presentation number)]

Thermoelectric Properties of Sb_2Te_3-based Ferecrystals based on Atomic Layer Deposition

*Kornelius Nielsch[1,2,3], Jun Yang[1], Dongho Shin[1], Sebastian Lehmann[1], Amin Bahrami[1]
[1] Leibniz Institute for Solid State and Materials Research, Dresden, Germany, [2] Institute of Material Science, Technical Univ. of Dresden, Germany, [3] Institute of Applied Physics, Technical Univ. of Dresden, Germany
*k.nielsch@ifw-dresden.de
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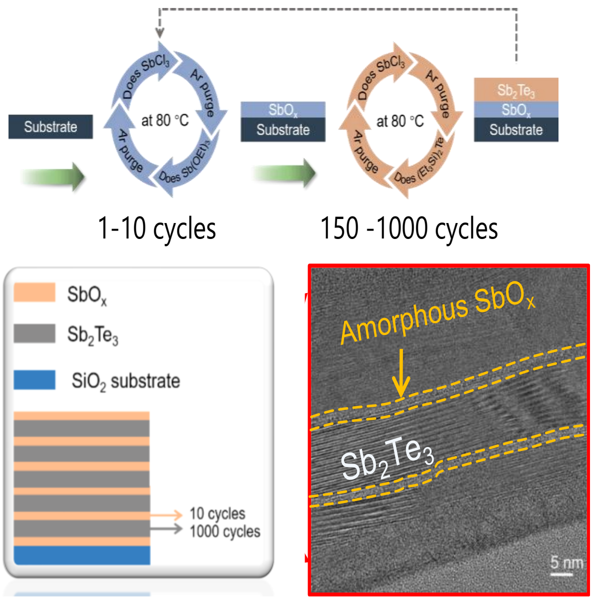
Atomic layer deposition is a very versatile technology for the deposition of thin films with precise thickness control on large areas, non-planar surfaces and 3D objects. The chemical reaction is surface limited, well defined and works in most cases at low temperatures (RT to 250 °C). For a number of classical van der Waals 2D materials, there have been reports on ALD of transition metal dichalcogenide (TMDC) of MoS_2, SnS_2, WS_2 and WSe_2, which also included the electronic characterization as a field effect transistor (FET).



In this work, we have fabricated by atomic layer deposition (ALD) multilayers of layered materials based on topological insulators and van der Waals materials, called *ferecrystals*. These ferecrystals can be tailored to exhibit unusual properties such as high electrical conductivity or low thermal conductivity or magnetic properties. A detailed ferecrystal study was performed on ferecrytals of Sb_2Te_3 and SbO_x, which has been grown at the same temperature as single layers of Sb_2Te_3. Without post-annealing, the electrical and thermoelectric characterisation of the highly ordered samples have been performed with the ZT-chip setup. In general, the carrier mobility is very high >150 Vs^2/cm^2 and is even improved when the thickness of the Sb_2Te_3 layers is reduced and the number of SbO_x layers (typically 2 nm thickness) is increased. Detailed XRD investigations have been performed and an enhanced crystalline order is observed in the ferecrystal system compared to individual layers of Sb_2Te_3. We have grown ferecrystals based on Sb_2Te_3 and Sb_2Se_3 with tetrahedral and orthorhombic crystal structure, respectively. The p-type hole carrier concentration of Sb_2Te_3 films can be enhanced through the sublayer doping of Sb_2Se_3. The highest carrier concentration achieved was 2.5×10^{19} cm^{-2} when the thickness ratio of Sb_2Te_3 to Sb_2Se_3 was (4 nm/2 nm). Further reduction of the Sb_2Te_3 thickness resulted in a high Seebeck coefficient of 172 µV/K at room temperature.

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